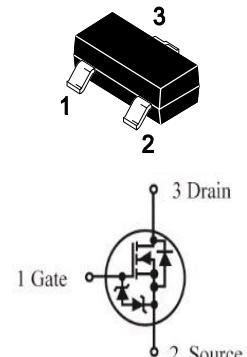


N-Channel Enhancement Mode MOSFET

Feature

- 50V/0.2A,RDS(ON)=3.5 Ω (MAX) @VGS=5V.Id=0.2A.
RDS(ON)=10Ω (MAX) @VGS=2.75V.Id=0.2A.
- Super High dense cell design for extremely low RDS(ON).
- Reliable and Rugged.
- Low Threshold Voltage (0.5V—1.5 V) Make it Ideal for Low Voltage Applications.
- ESD protected.
- SOT-23 for Surface Mount Package.



SOT23

Applications

Power Management in DC/DC Converters、 Portable and Battery-powered Products.

Absolute Maximum Ratings

TA=25 °C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	VDS	50	V
Gate-Source Voltage	VGS	±20	V
Drain Current-Continuous	ID	0.2	A

Electrical Characteristics

TA=25 °C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-source Voltage	BVDSS	VGS=0V, ID=250μA	50	-	-	V
Zero-Gate Voltage Drain Current	IGSS	VDS=50V, VGS=0V	-	-	0.5	μA
		VDS=25V, VGS=0V	-	-	0.1	
Gate Body Leakage Current, Forward	IGSSF	VGS=20V, VDS=0V	-	-	300	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-20V, VDS=0V	-	-	-300	nA
On Characteristics						
Gate Threshold Voltage	VGS(TH)	VGS= VDS, ID=1.0 mA	0.5	-	1.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS =5.0V, ID =0.2A	-	-	3.5	Ω
		VGS =2.75V, ID =0.2A	-	-	10	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Diode Forward Voltage	VSD	VGS =2.75V, ID =0.2A			2.5	V

Typical Characteristics

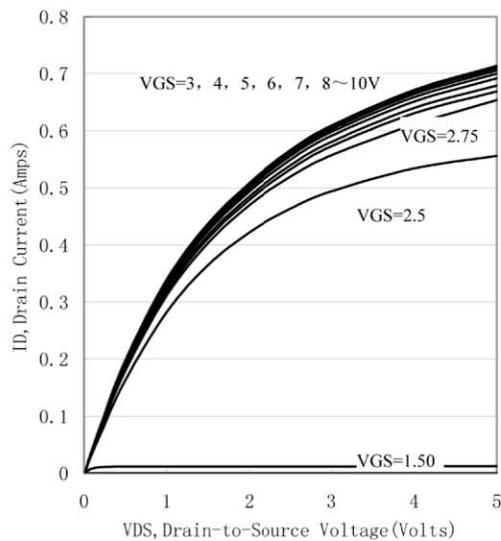


Figure 1. Output Characteristics

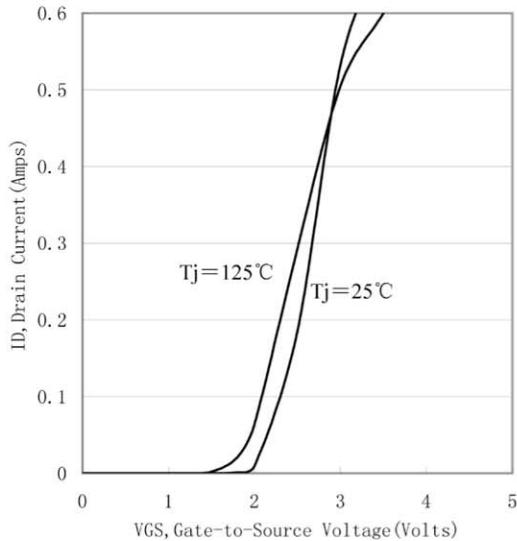


Figure 2. Transfer Characteristics

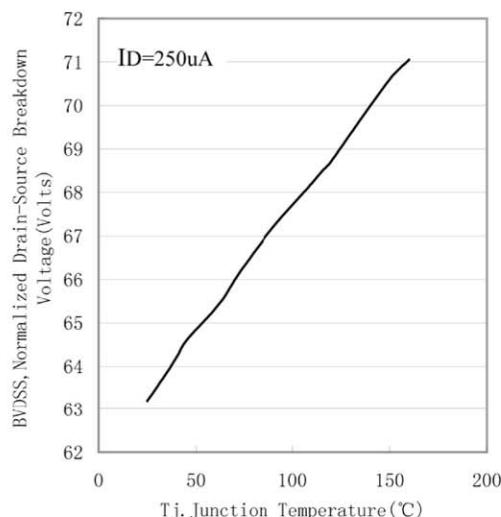


Figure 3. Breakdown Voltage Variation with Temperature

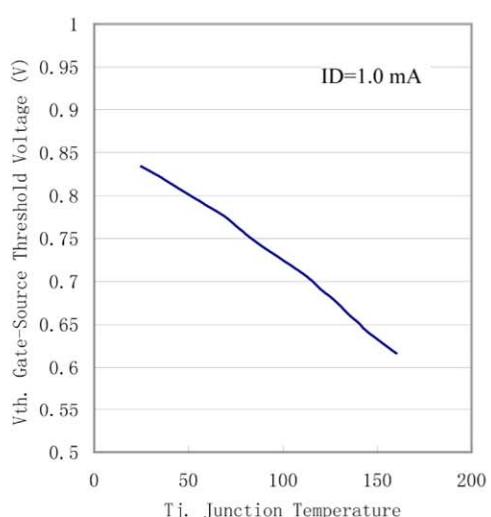


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

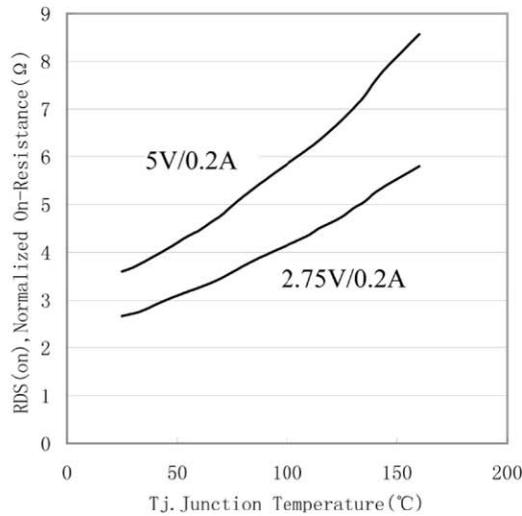


Figure 5. On-Resistance Variation with Temperature

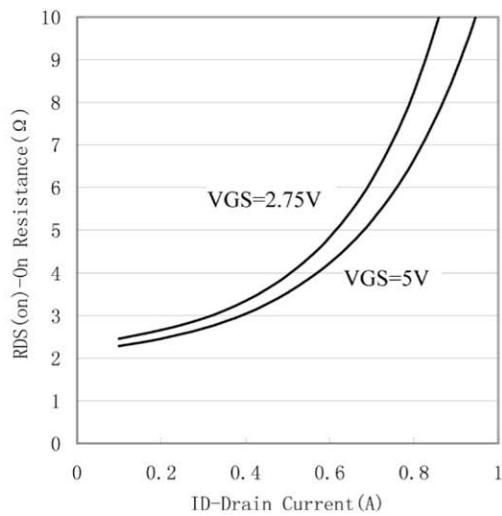


Figure 6. On-Resistance vs. Drain Current

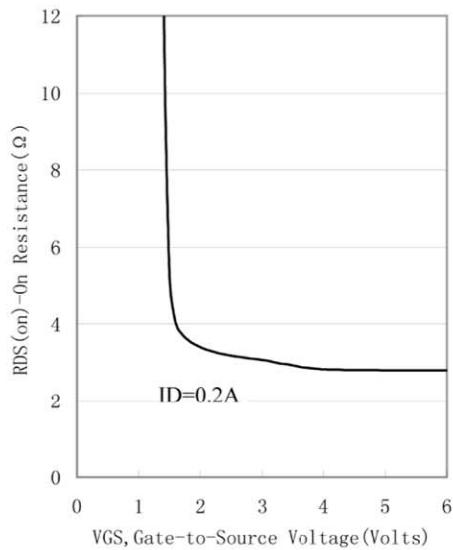


Figure 7. On-Resistance vs. Gate-to-Source Voltage

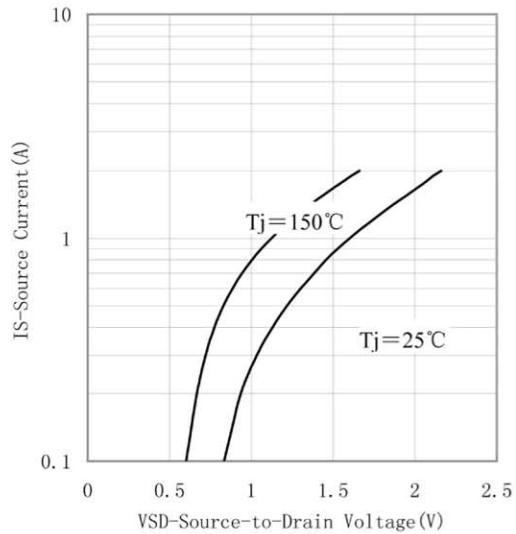


Figure 8. Source-Drain Diode Forward Voltage